

XN4502

Silicon NPN epitaxial planer transistor

For general amplification

Features

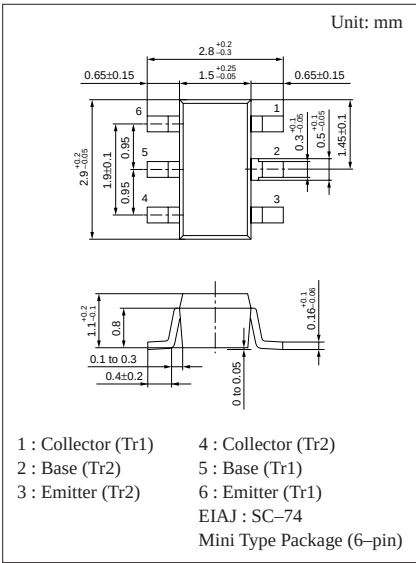
- Two elements incorporated into one package.
- Reduction of the mounting area and assembly cost by one half.

Basic Part Number of Element

- 2SD602A × 2 elements

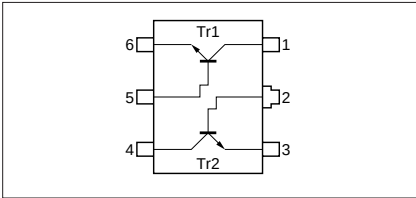
Absolute Maximum Ratings (Ta=25°C)

	Parameter	Symbol	Ratings	Unit
Rating of element	Collector to base voltage	V_{CBO}	60	V
	Collector to emitter voltage	V_{CEO}	50	V
	Emitter to base voltage	V_{EBO}	5	V
	Collector current	I_C	0.5	A
	Peak collector current	I_{CP}	1	A
Overall	Total power dissipation	P_T	300	mW
	Junction temperature	T_j	150	°C
	Storage temperature	T_{sig}	-55 to +150	°C



Marking Symbol: 5Q

Internal Connection

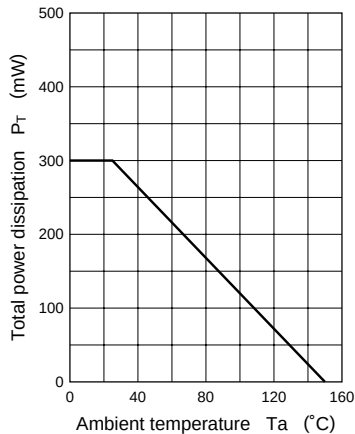


Electrical Characteristics (Ta=25°C)

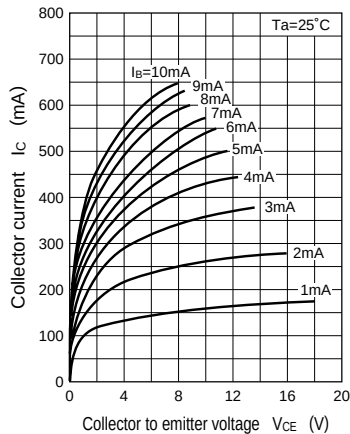
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V_{CBO}	$I_C = 10\mu A, I_E = 0$	60			V
Collector to emitter voltage	V_{CEO}	$I_C = 2mA, I_B = 0$	50			V
Emitter to base voltage	V_{EBO}	$I_E = 10\mu A, I_C = 0$	5			V
Collector cutoff current	I_{CBO}	$V_{CB} = 20V, I_E = 0$			0.1	μA
Forward current transfer ratio	h_{FE1}	$V_{CE} = 10V, I_C = 150mA^*$	85		340	
	h_{FE2}	$V_{CE} = 10V, I_C = 500mA^*$	40			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 300mA, I_B = 30mA^*$		0.35	0.6	V
Transition frequency	f_T	$V_{CB} = 10V, I_E = -50mA, f = 200MHz$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		6	15	pF

* Pulse measurement

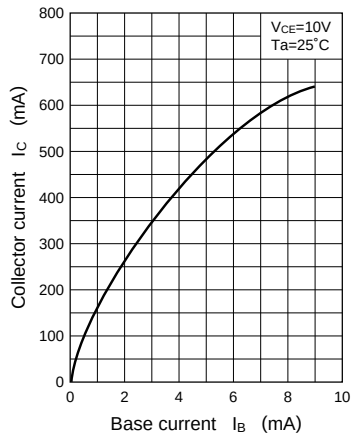
$P_T - T_a$



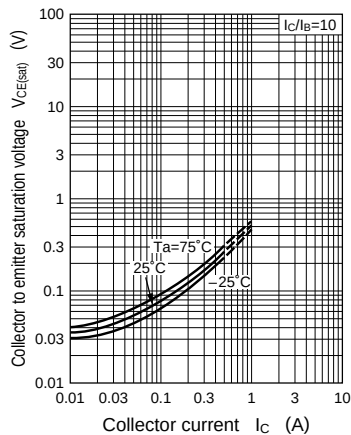
$I_C - V_{CE}$



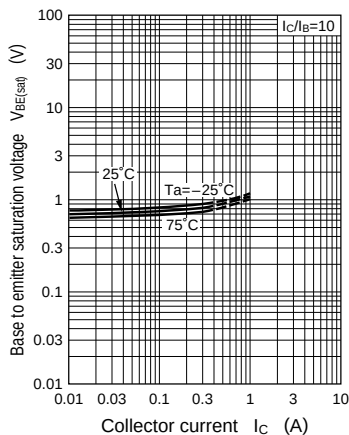
$I_C - I_B$



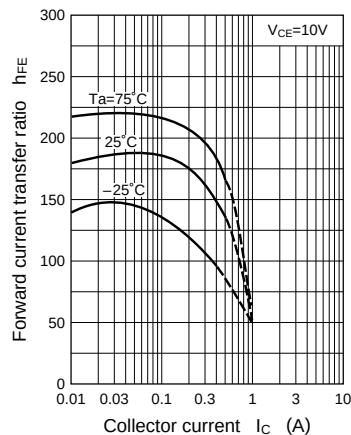
$V_{CE(sat)} - I_C$



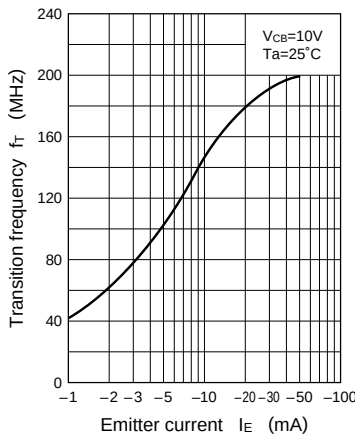
$V_{BE(sat)} - I_C$



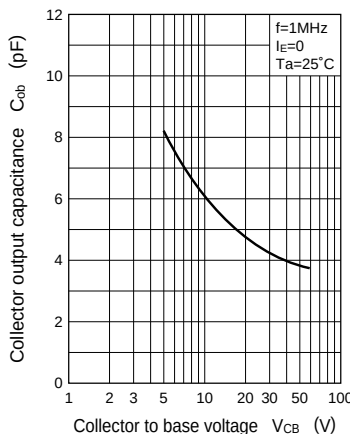
$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$



$V_{CER} - R_{BE}$

